









	<h2 style="color: red;">FQB2N80TM</h2>	
	<b>Hersteller-Teilenummer:</b>	<a href="#">FQB2N80TM</a>
	<b>Hersteller / Marke:</b>	<a href="#">AMI Semiconductor / ON Semiconductor</a>
	<b>Teil der Beschreibung:</b>	MOSFET N-CH 800V 2.4A D2PAK
<b>Datenblätter:</b>	 <a href="#">FQB2N80TM.pdf</a>	
<b>RoHs Status:</b>	Bleifrei / RoHS-konform	
<b>Lagerzustand:</b>	New original, 700 pcs Stock Available.	
<b>Liefern von:</b>	Hong Kong	
<b>Versandweg:</b>	DHL/Fedex/TNT/UPS/EMS	
Image may be representation. See specs for product details.		

### Spezifikationen

Teilenummer	<a href="#">FQB2N80TM</a>
Hersteller	<a href="#">AMI Semiconductor / ON Semiconductor</a>
Beschreibung	MOSFET N-CH 800V 2.4A D2PAK
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	700 pcs Stock
detaillierte Beschreibung	N-Channel 800V 2.4A (Tc) 3.13W (Ta), 85W (Tc)
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D <sup>2</sup> Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D <sup>2</sup> PAK (TO-263AB)
Verlustleistung (max)	3.13W (Ta), 85W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	800V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	2.4A (Tc)
Rds On (Max) @ Id, Vgs	6.3 Ohm @ 900mA, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	15nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	550pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±30V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)

FQB2N80TM ist neu im Original, Suche FQB2N80TM Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQB2N80TM AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage FQB2N80TM: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>FQB2N80</b> Fairchild/ON Semiconductor FQB2N80 FAIRCHILD</p>	 <p><b>FQB2NA90TM</b> Fairchild/ON Semiconductor MOSFET N-CH 900V 2.8A D2PAK</p>	 <p><b>FQB2N90TM</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 900V 2.2A D2PAK</p>	 <p><b>FQB2N80TM</b> Fairchild/ON Semiconductor MOSFET N-CH 800V 2.4A D2PAK</p>
 <p><b>FQB2NA90TM</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 900V 2.8A D2PAK</p>	 <p><b>FQB2N60TM</b> Fairchild/ON Semiconductor MOSFET N-CH 600V 2.4A D2PAK</p>	 <p><b>FQB2N50TM</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 500V 2.1A D2PAK</p>	 <p><b>FQB2N90TM</b> Fairchild/ON Semiconductor MOSFET N-CH 900V 2.2A D2PAK</p>

### heiße Teile

Mehr

 FQB19N20LTM	 FQB19N20TM	 FQB19N20TM	 FQB1N60TM	 FQB1N60TM
 FQB20N06L	 FQB20N60FTM	 FQB20N60TM	 FQB22P10	 FQB22P10TM
 FQB22P10TM	 FQB22P10TM_F085	 FQB24N08TM	 FQB24N08TM	 FQB25N33
 FQB25N33TM	 FQB25N33TM	 FQB25N33TM_F085	 FQB27N25TM	 FQB27P06
 FQB27P06TM	 FQB27P06TM	 FQB2N50C	 FQB2N60TM	 FQB2N60TM
 FQB2N80TM	 FQB2NA90TM	 FQB2NA90TM	 FQB2P25TM	 FQB2P25TM
 FQB30N06	 FQB30N06L	 FQB30N06LTM	 FQB30N06LTM	 FQB30N06TM
 FQB30N06TM	 FQB32N12V2	 FQB32N12V2TM	 FQB32N12V2TM	 FQB32N20
 FQB32N20C	 FQB32N20CTM	 FQB32N20CTM	 FQB32N30	 FQB33N10
 FQB33N10L	 FQB33N10LTM	 FQB33N10LTM	 FQB33N10TM	 FQB33N10TM

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

Copyright © 2019 YIC International Co., Limited